

Dual N-channel 100 V, 27.5 mΩ standard level MOSFET

2 September 2015

Product data sheet

1. General description

Dual Standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quie	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	29	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	64	W
Static characte	eristics FET1 and FET2						-
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>		-	21.5	27.5	mΩ
Dynamic characteristics FET1 and FET2							
Q _{GD}	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 13}}{13}; \frac{\text{Fig. 14}}{14}$		-	12.9	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	
2	G1	gate1		
3	S2	source2	\bigcirc	
4	G2	gate2		
5	D2	drain2		 S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1	(0011200)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK7K32-100E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7K32-100E	73210E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	64	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	-	29	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u>	-	20.4	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; Fig. 3	-	116	А
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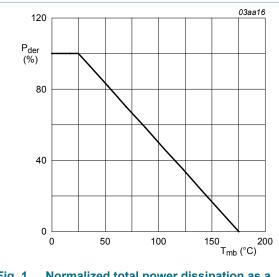
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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain	n diode FET1 and FET2		·			
I _S	source current	T _{mb} = 25 °C		-	29	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	116	А
Avalanche R	uggedness FET1 and FET2					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} {\sf I}_D = 29 \; {\sf A}; {\sf V}_{sup} \le 100 \; {\sf V}; {\sf R}_{GS} = 50 \; \Omega; \\ {\sf V}_{GS} = 10 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; {\rm ^{\circ}C}; \; unclamped; \\ \hline {\sf Fig. 4} \end{array}$	[1][2]	-	67	mJ

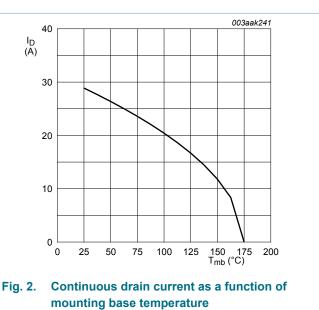
[1] Refer to application note AN10273 for further information

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C





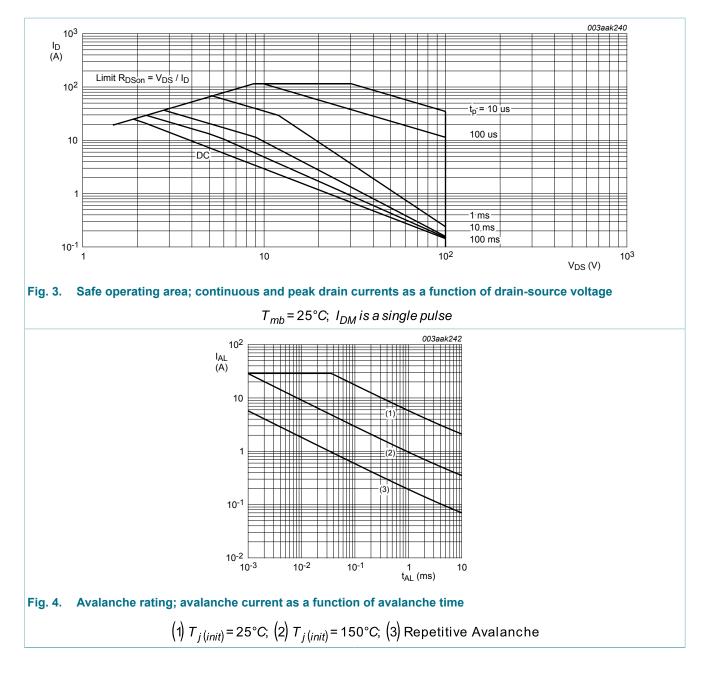
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



V_{GS}≥10V

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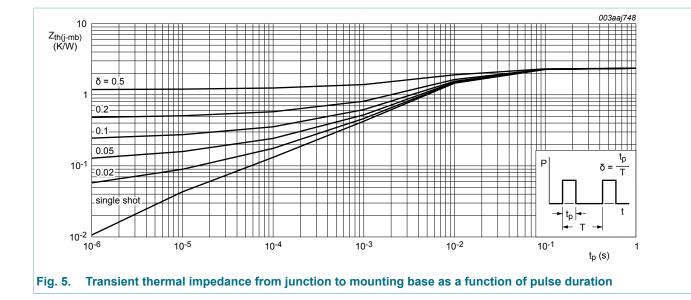
9. Thermal characteristics

Table 6. The	rmai characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	2.36	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

Table 6. Thermal characteristics

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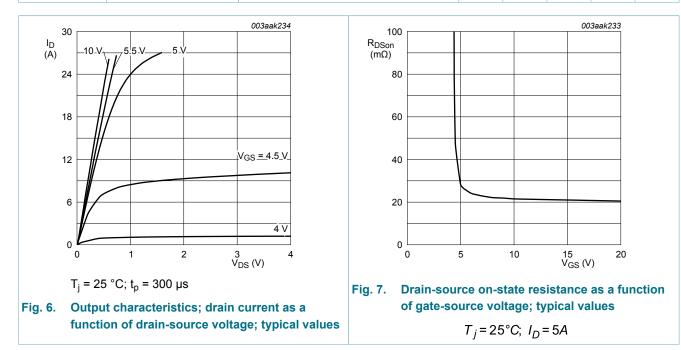
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics FET1 and FET2					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10	1	-	-	V	
	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	4.5	V	
I _{DSS}		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	21.5	27.5	mΩ
resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 11; Fig. 12	-	55	76	mΩ	
Dynamic ch	naracteristics FET1 and FE	T2	1			
Q _{G(tot)}	total gate charge	I_D = 5 A; V_{DS} = 80 V; V_{GS} = 10 V;	-	34	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	6.5	-	nC
Q _{GD}	gate-drain charge		-	12.9	-	nC

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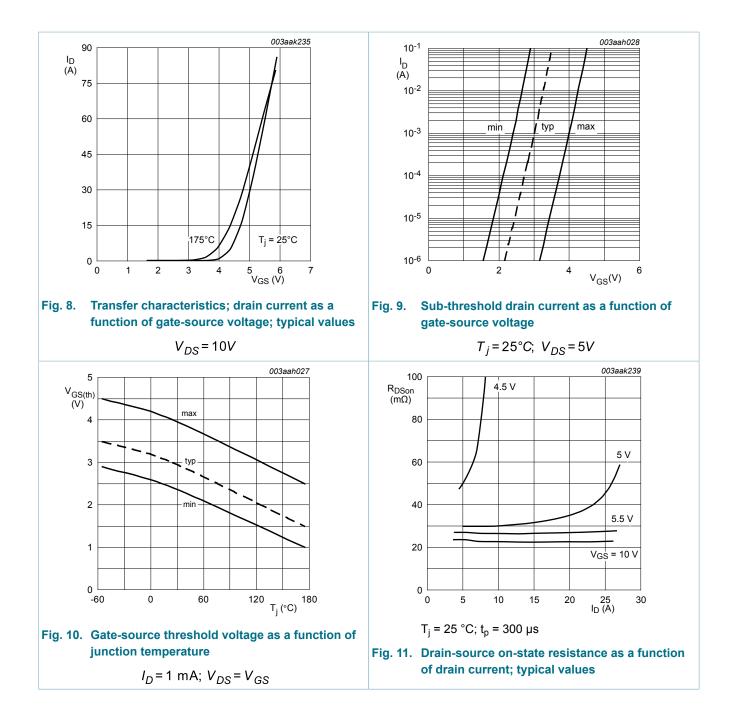
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	1603	2137	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	164	196	pF
C _{rss}	reverse transfer capacitance	V _{DS} = 80 V; R _L = 15 Ω; V _{GS} = 10 V; R _{G(ext)} = 5 Ω; T _j = 25 °C	-	109	150	pF
t _{d(on)}	turn-on delay time		-	7.8	-	ns
t _r	rise time		-	10.9	-	ns
t _{d(off)}	turn-off delay time		-	24.2	-	ns
t _f	fall time		-	13.8	-	ns
Source-dra	in diode FET1 and FET2	1			1	
V _{SD}	source-drain voltage	$I_{S} = 5 \text{ A}; V_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}; \text{ Fig. 16}$	-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 5 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	35.9	-	ns
Q _r	recovered charge	V _{DS} = 50 V; T _j = 25 °C	-	52.8	-	nC



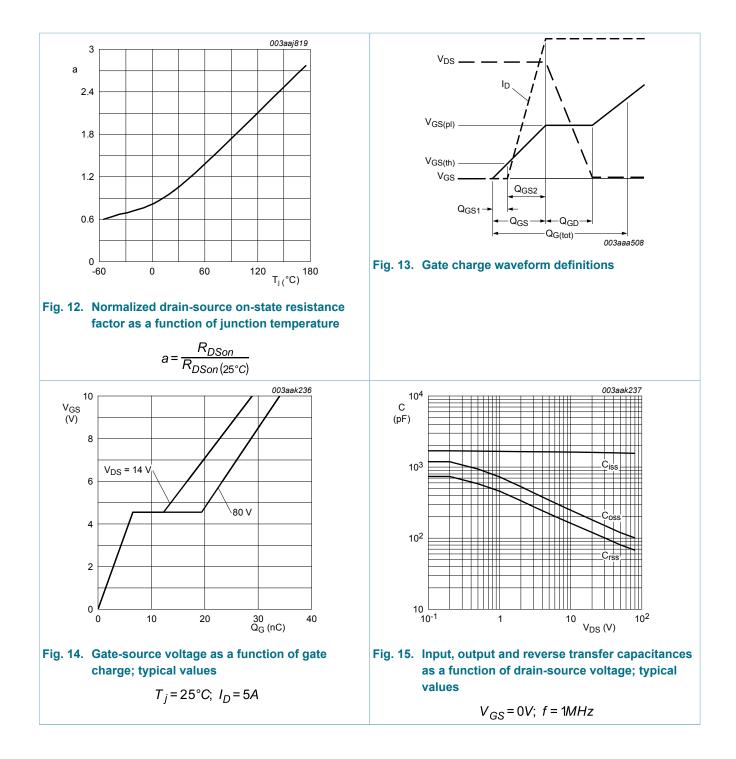
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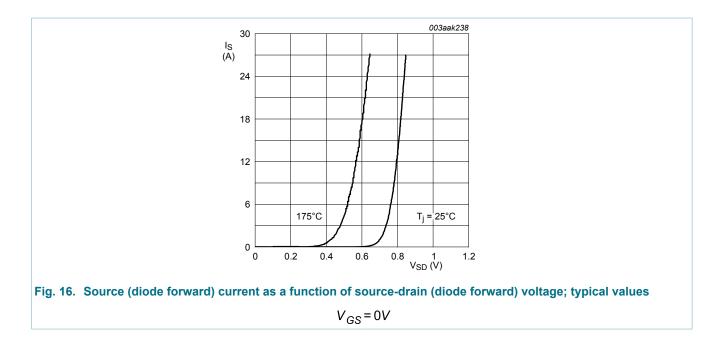
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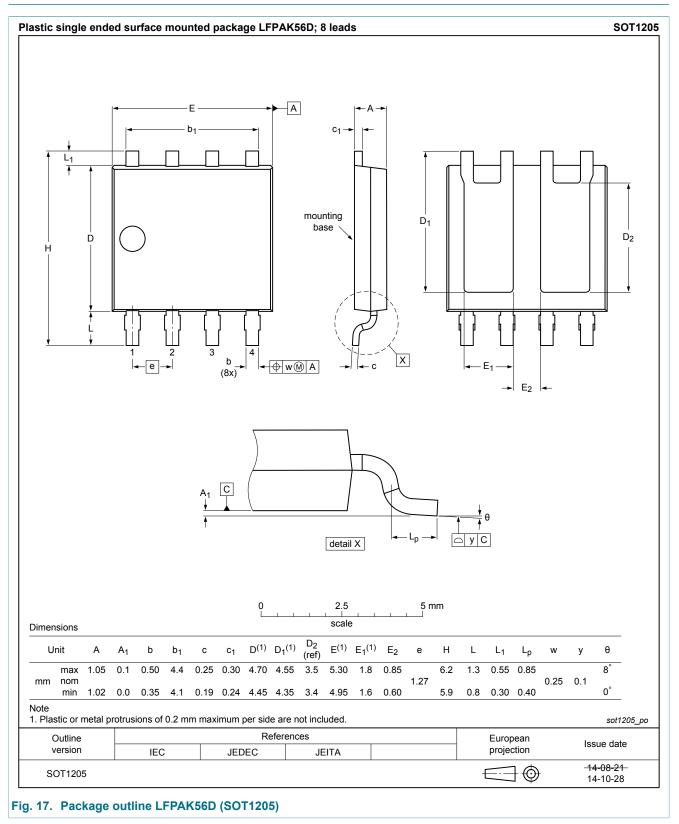
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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